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PHASE CONTROL THYRISTOR

AT620

Repetitive voltage up to

1400 V

Mean on-state current

2100 A

Surge current

36 kA

TARGET SPECIFICATION

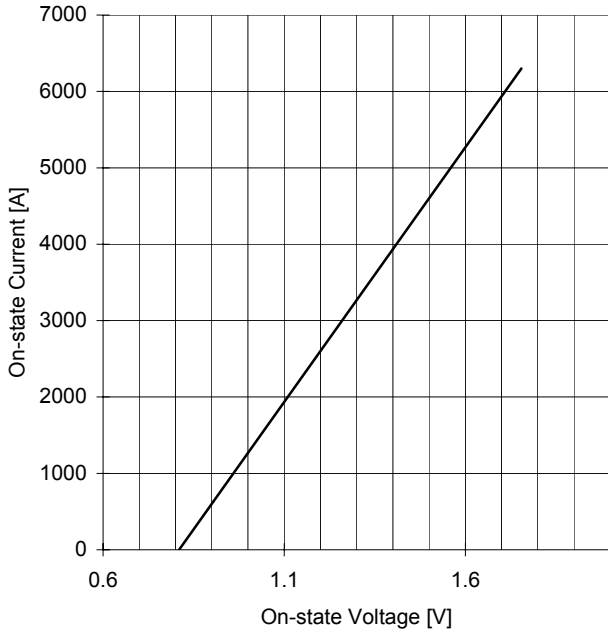
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Symbol	Characteristic	Conditions	T _j [°C]	Value	Unit
BLOCKING					
V _{RRM}	Repetitive peak reverse voltage		125	1400	V
V _{RSM}	Non-repetitive peak reverse voltage		125	1500	V
V _{DRM}	Repetitive peak off-state voltage		125	1400	V
I _{RRM}	Repetitive peak reverse current	V=VRRM	125	100	mA
I _{DRM}	Repetitive peak off-state current	V=VDRM	125	100	mA
CONDUCTING					
I _{T(AV)}	Mean on-state current	180° sin, 50 Hz, Th=55°C, double side cooled		2100	A
I _{T(AV)}	Mean on-state current	180° sin, 50 Hz, Tc=85°C, double side cooled		1805	A
I _{TSM}	Surge on-state current	sine wave, 10 ms	125	36	kA
I ² t	I ² t	without reverse voltage		6480 x1E3	A ² s
V _T	On-state voltage	On-state current = 2900 A	25	1.3	V
V _{T(TO)}	Threshold voltage		125	0.81	V
r _T	On-state slope resistance		125	0.150	mohm
SWITCHING					
di/dt	Critical rate of rise of on-state current, min.	From 75% VDRM up to 2200 A, gate 10V 5ohm	125	200	A/μs
dv/dt	Critical rate of rise of off-state voltage, min.	Linear ramp up to 70% of VDRM	125	500	V/μs
t _d	Gate controlled delay time, typical	VD=100V, gate source 25V, 10 ohm, tr=.5 μs	25	3	μs
t _q	Circuit commutated turn-off time, typical	dV/dt = 20 V/μs linear up to 75% VDRM		250	μs
Q _{rr}	Reverse recovery charge	di/dt=-20 A/μs, I= 1430 A	125		μC
I _{rr}	Peak reverse recovery current	VR= 50 V			A
I _H	Holding current, typical	VD=5V, gate open circuit	25	300	mA
I _L	Latching current, typical	VD=5V, tp=30μs	25	700	mA
GATE					
V _{GT}	Gate trigger voltage	VD=5V	25	3.5	V
I _{GT}	Gate trigger current	VD=5V	25	300	mA
V _{GD}	Non-trigger gate voltage, min.	VD=VDRM	125	0.25	V
V _{FGM}	Peak gate voltage (forward)			30	V
I _{FGM}	Peak gate current			10	A
V _{RGM}	Peak gate voltage (reverse)			5	V
P _{GM}	Peak gate power dissipation	Pulse width 100 μs		150	W
P _G	Average gate power dissipation			2	W
MOUNTING					
R _{th(j-h)}	Thermal impedance, DC	Junction to heatsink, double side cooled		21	°C/kW
R _{th(c-h)}	Thermal impedance	Case to heatsink, double side cooled		6	°C/kW
T _j	Operating junction temperature			-30 / 125	°C
F	Mounting force			22.0 / 24.5	kN
	Mass			520	g
ORDERING INFORMATION : AT620 S 14					
standard specification <input type="checkbox"/> VDRM&VRRM/100 <input type="checkbox"/>					

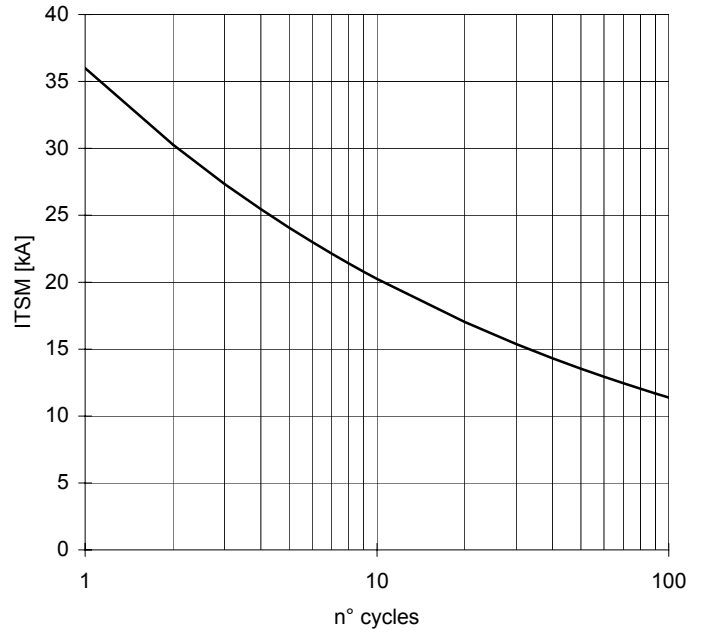
AT620 PHASE CONTROL THYRISTOR

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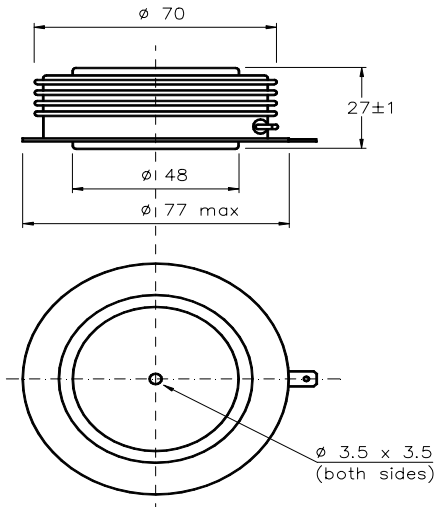
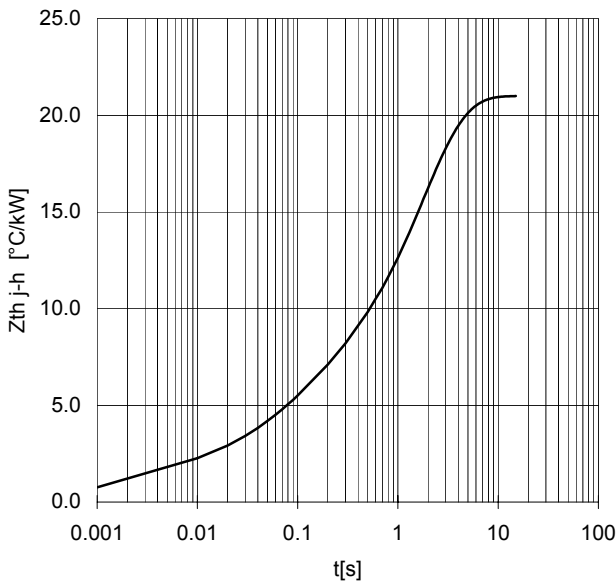
ON-STATE CHARACTERISTIC
 $T_j = 125^\circ\text{C}$



SURGE CHARACTERISTIC
 $T_j = 125^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE
 DOUBLE SIDE COOLED



Dimensions
 in mm



Cathode terminal type DIN 46244 - A 4.8 - 0.8

Gate terminal type AMP 60598 - 1

All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 μm .

In the interest of product improvement ANSALDO reserves the right to change any data given in this data sheet at any time without previous notice.

If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

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